

A cross-sectional view of a semiconductor device 10. The device features a substrate 16 with a base layer 18. A series of vertical structures 14 are formed on the substrate, each containing a central core 22. The top of the device is covered by a layer 24, which has a series of rectangular openings 26. A layer 30 is formed on top of the openings 26, and a layer 32 is formed on top of the layer 30. A dashed line 12 indicates a cross-section through the device, and a dashed line 36 indicates a cross-section through the substrate 16.

FIG. 2